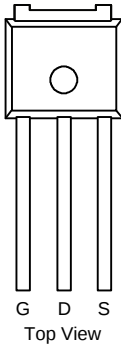


N-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY

V_{DS}	30	V
$R_{DS(on)}$ $V_{GS} = 10\text{ V}$	3.5	$m\Omega$
$R_{DS(on)}$ $V_{GS} = 4.5\text{ V}$	4.5	$m\Omega$
I_D	100	A
Configuration	Single	

TO-251



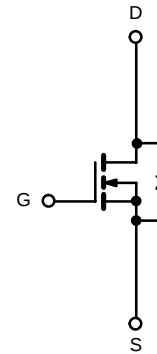
FEATURES

- Trench Power MOSFET
- 100 % R_g and UIS Tested
- Compliant to RoHS Directive 2011/65/EU


RoHS
 COMPLIANT

APPLICATIONS

- OR-ing
- Server
- DC/DC



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ($T_J = 175\text{ }^\circ\text{C}$)	I_D	$T_C = 25\text{ }^\circ\text{C}$ 100 ^{a, e}	A
		$T_C = 70\text{ }^\circ\text{C}$ 95 ^e	
		$T_A = 25\text{ }^\circ\text{C}$ 35 ^{b, c}	
		$T_A = 70\text{ }^\circ\text{C}$ 26 ^{b, c}	
Pulsed Drain Current	I_{DM}	197	mJ
Avalanche Current Pulse	I_{AS}	39	
Single Pulse Avalanche Energy	E_{AS}	94.8	
Continuous Source-Drain Diode Current	I_S	$T_C = 25\text{ }^\circ\text{C}$ 90 ^{a, e}	A
		$T_A = 25\text{ }^\circ\text{C}$ 3.13 ^{b, c}	
Maximum Power Dissipation	P_D	$T_C = 25\text{ }^\circ\text{C}$ 250 ^a	W
		$T_C = 70\text{ }^\circ\text{C}$ 175	
		$T_A = 25\text{ }^\circ\text{C}$ 3.75 ^{b, c}	
		$T_A = 70\text{ }^\circ\text{C}$ 2.63 ^{b, c}	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 175	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typ.	Max.	Unit
Maximum Junction-to-Ambient ^{b, d}	R_{thJA}	32	40	$^\circ\text{C/W}$
Maximum Junction-to-Case	R_{thJC}	0.5	0.6	

Notes:

a. Based on $T_C = 25\text{ }^\circ\text{C}$.

b. Surface mounted on 1" x 1" FR4 board.

c. $t = 10\text{ sec}$.d. Maximum under steady state conditions is 90 $^\circ\text{C/W}$.

e. Calculated based on maximum junction temperature. Package limitation current is 90 A.

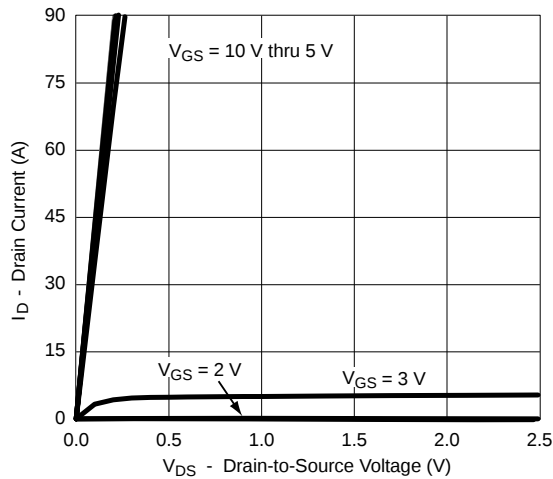
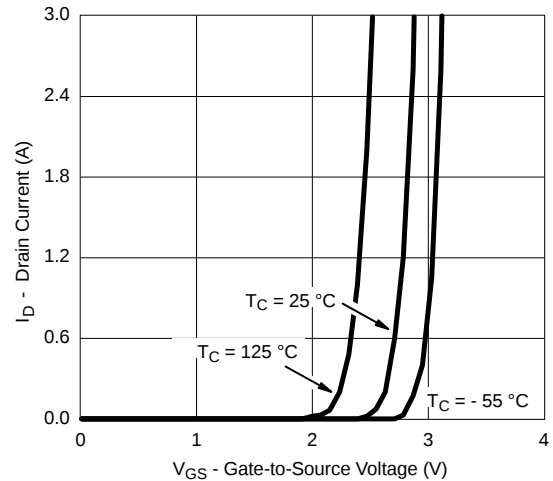
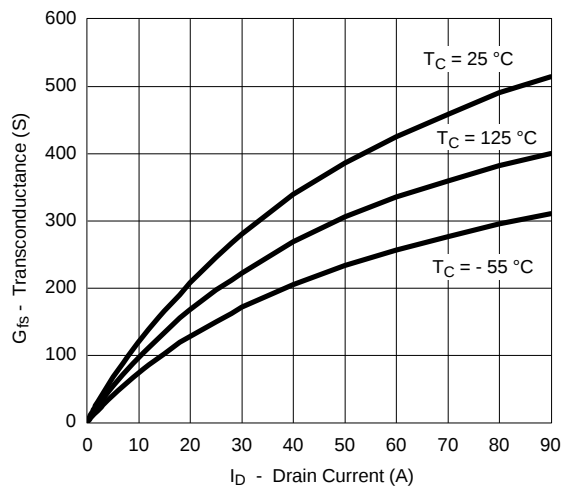
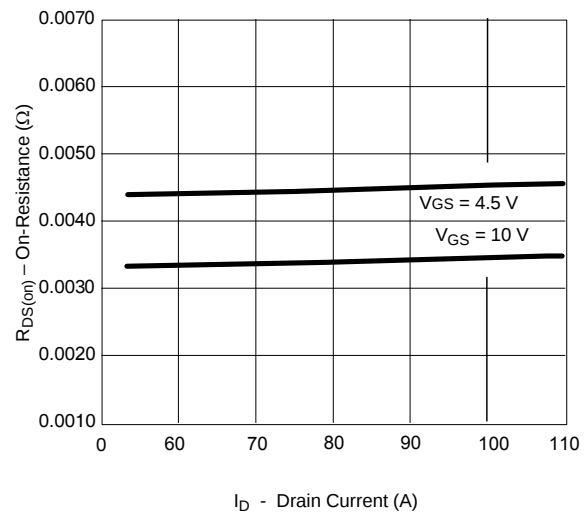
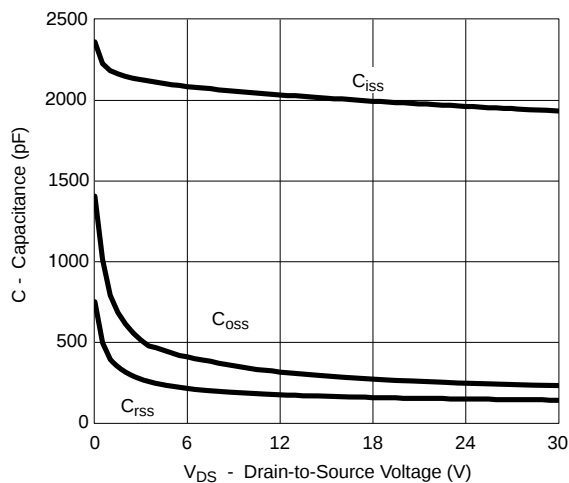
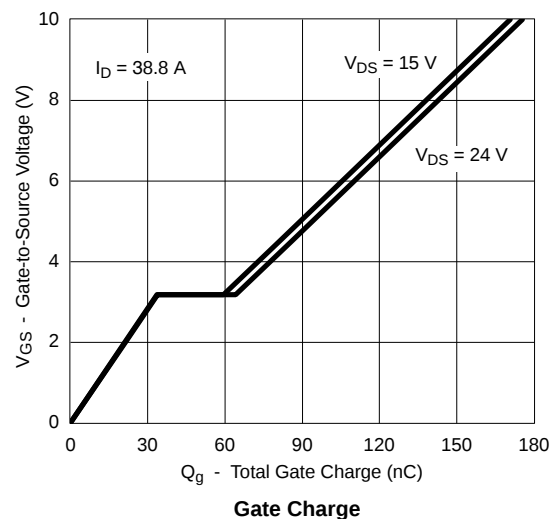
SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	30			V
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = 250 μA		35		mV/°C
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)} /T _J			- 7.5		
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	1.0		2.5	V
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V			1	μA
		V _{DS} = 30 V, V _{GS} = 0 V, T _J = 55 °C			10	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = 10 V	90			A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 38.8 A		3.5		mΩ
		V _{GS} = 4.5 V, I _D = 37 A		4.5		
Forward Transconductance ^a	g _{fs}	V _{DS} = 15 V, I _D = 38.8 A		160		S
Dynamic ^b						
Input Capacitance	C _{iss}	V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz		3000		pF
Output Capacitance	C _{oss}			710		
Reverse Transfer Capacitance	C _{rss}			170		
Total Gate Charge	Q _g	V _{DS} = 15 V, V _{GS} = 10 V, I _D = 38.8 A		170		nC
		V _{DS} = 15 V, V _{GS} = 4.5 V, I _D = 28.8 A		81.5		
Gate-Source Charge	Q _{gs}			34		
Gate-Drain Charge	Q _{gd}			29		
Gate Resistance	R _g	f = 1 MHz		1.4	2.1	Ω
Turn-On Delay Time	t _{d(on)}	V _{DD} = 15 V, R _L = 0.625 Ω I _D ≅ 24 A, V _{GEN} = 10 V, R _g = 1 Ω		18	27	ns
Rise Time	t _r			11	17	
Turn-Off Delay Time	t _{d(off)}			70	105	
Fall Time	t _f			10	15	
Turn-On Delay Time	t _{d(on)}	V _{DD} = 15 V, R _L = 0.67 Ω I _D ≅ 22.5 A, V _{GEN} = 4.5 V, R _g = 1 Ω		55	83	
Rise Time	t _r			180	270	
Turn-Off Delay Time	t _{d(off)}			55	83	
Fall Time	t _f			12	18	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			120	A
Pulse Diode Forward Current ^a	I _{SM}				120	
Body Diode Voltage	V _{SD}	I _S = 22 A		0.8	1.2	V
Body Diode Reverse Recovery Time	t _{rr}	I _F = 20 A, di/dt = 100 A/μs, T _J = 25 °C		52	78	ns
Body Diode Reverse Recovery Charge	Q _{rr}			70.2	105	nC
Reverse Recovery Fall Time	t _a			27		ns
Reverse Recovery Rise Time	t _b			25		

Notes:

a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Output Characteristics

Transfer Characteristics

Transconductance

 $R_{DS(on)}$ vs. Drain Current

Capacitance


TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



On-Resistance vs. Junction Temperature



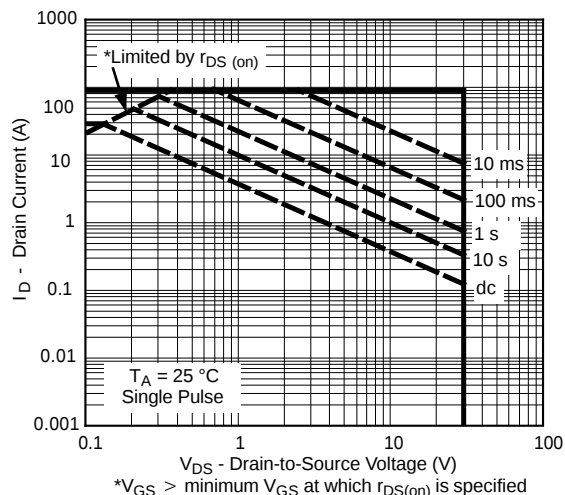
Forward Diode Voltage vs. Temperature



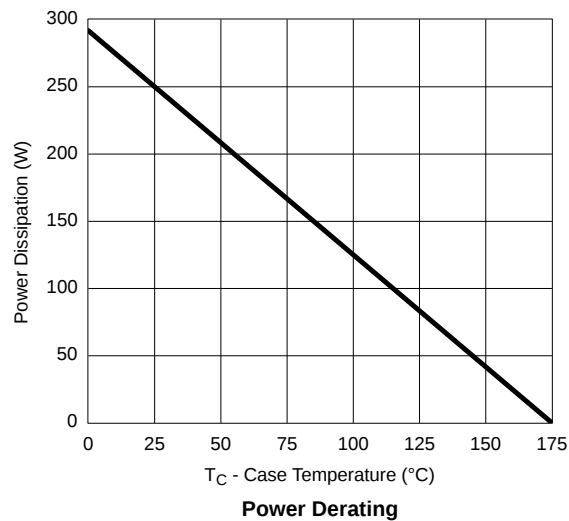
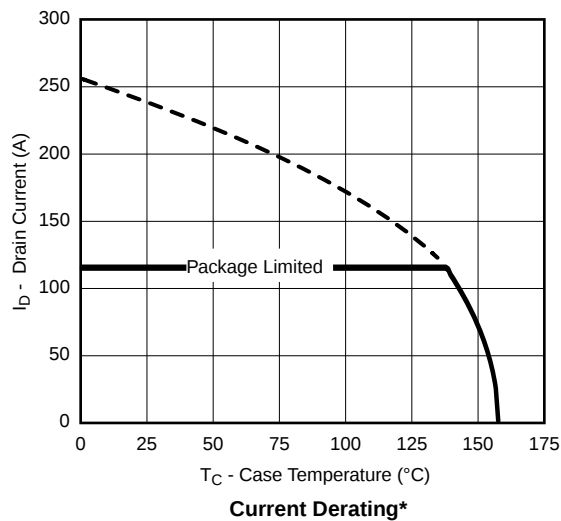
$R_{DS(on)}$ vs. V_{GS} vs. Temperature



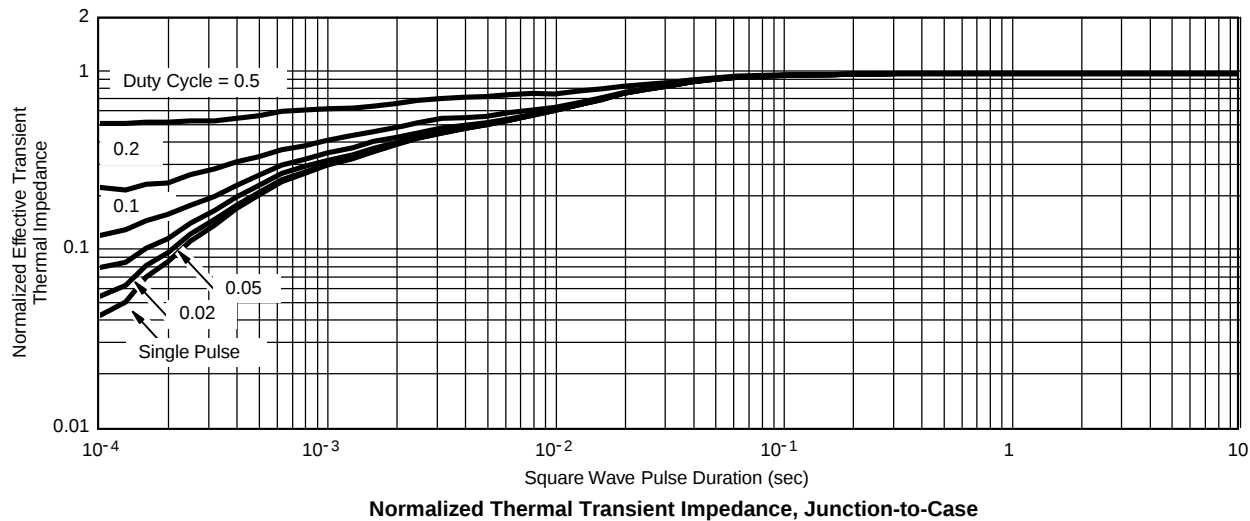
Threshold Voltage



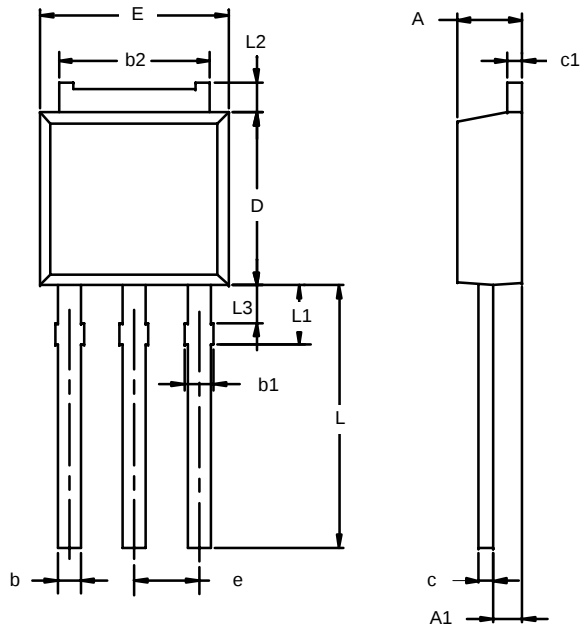
Safe Operating Area, Junction-to-Ambient

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)


*The power dissipation P_D is based on $T_{J(max)} = 175$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



TO-251AA (DPAK)



Note: Dimension L3 is for reference only.

Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	2.21	2.38	0.087	0.094
A1	0.89	1.14	0.035	0.045
b	0.71	0.89	0.028	0.035
b1	0.76	1.14	0.030	0.045
b2	5.23	5.43	0.206	0.214
c	0.46	0.58	0.018	0.023
c1	0.46	0.58	0.018	0.023
D	5.97	6.22	0.235	0.245
E	6.48	6.73	0.255	0.265
e	2.28 BSC		0.090 BSC	
L	8.89	9.53	0.350	0.375
L1	1.91	2.28	0.075	0.090
L2	0.89	1.27	0.035	0.050
L3	1.15	1.52	0.045	0.060
ECN: S-03946—Rev. E, 09-Jul-01 DWG: 5346				

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